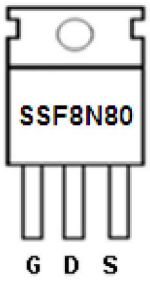
SSF8N80

800V N-Channel MOSFET

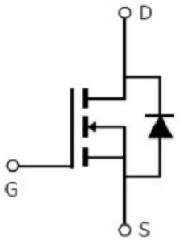
Main Product Characteristics

V_{DSS}	800V
R_{DS}(on)	1.38Ω(typ.)
I_D	8A

TO-220



Marking and Pin Assignment



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150℃ operating temperature
- Lead free product

Description

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V①	8	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V①	5.1	
I_{DM}	Pulsed Drain Current②	32	
P_D @T_C = 25°C	Power Dissipation③	178	W
	Linear Derating Factor	1.43	W/°C
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy @ L=25mH	512	mJ
I_{AS}	Avalanche Current @ L=25mH	6.4	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

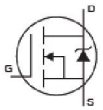
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case③	—	0.7	℃/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ④	—	62.5	℃/W

Electrical Characteristics @T_A=25℃ unless otherwise specified

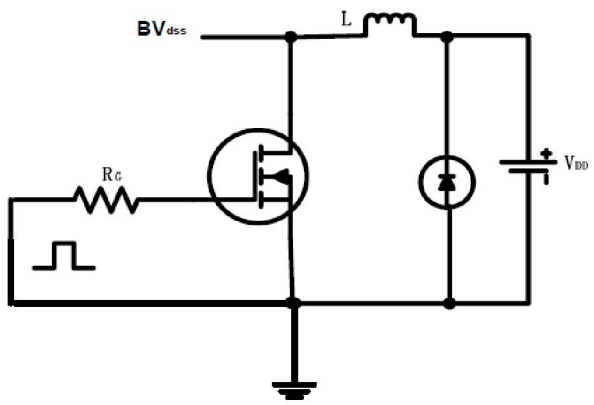
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	800	—	—	V	V_{GS} = 0V, ID = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.38	1.55	Ω	V_{GS}=10V,I_D = 3.5A
		—	3.16	—		T_J = 125℃
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	V_{DS} = V_{GS}, I_D = 250μA
		—	1.96	—		T_J = 125℃
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} = 800V,V_{GS} = 0V
		—	—	50		T_J = 125℃
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =30V
		—	—	-100		V_{GS} = -30V
Q_g	Total gate charge	—	24	—	nC	I_D = 8A,
Q_{gs}	Gate-to-Source charge	—	7.3	—		V_{DS}= 380V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	9.4	—		V_{GS} = 10V
$t_{d(on)}$	Turn-on delay time	—	20	—	ns	V_{GS}=10V, VDS=400V,
t_r	Rise time	—	40	—		R_L=50Ω,R_{GEN}=25Ω
$t_{d(off)}$	Turn-Off delay time	—	57	—		ID=8A
t_f	Fall time	—	35	—		
C_{iss}	Input capacitance	—	1107	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	120	—		V_{DS} = 25V
C_{rss}	Reverse transfer capacitance	—	4.7	—		f = 1MHz

Source-Drain Ratings and Characteristics

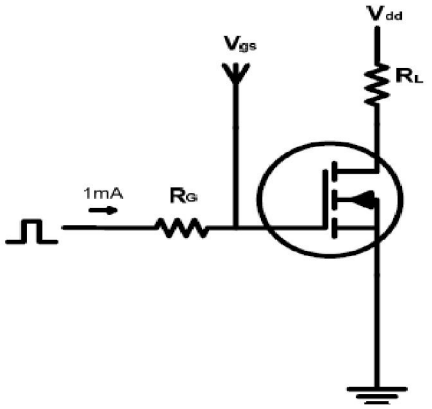
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	32	A	
V_{SD}	Diode Forward Voltage	—	0.87	1.4	V	I_S=7A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	—	1015	—	ns	T_J = 25°C, I_F =8A, di/dt = 100A/μs
Q_{rr}	Reverse Recovery Charge	—	5414	—	nC	

Test Circuits and Waveforms

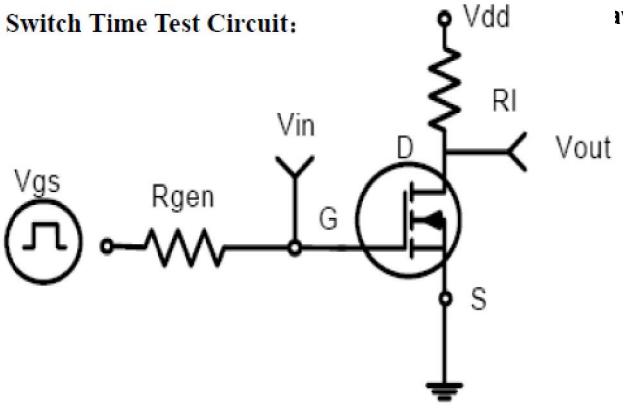
EAS test circuits:



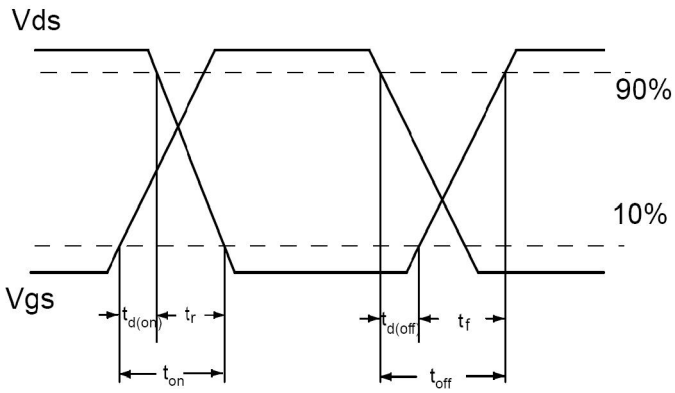
Gate charge test circuit:



Switch Time Test Circuit:



Waveforms:



Notes:

①The maximum current rating is limited by bond-wires.

②Repetitive rating; pulse width limited by max. junction temperature.

③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

④The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C

Typical Electrical and Thermal Characteristics

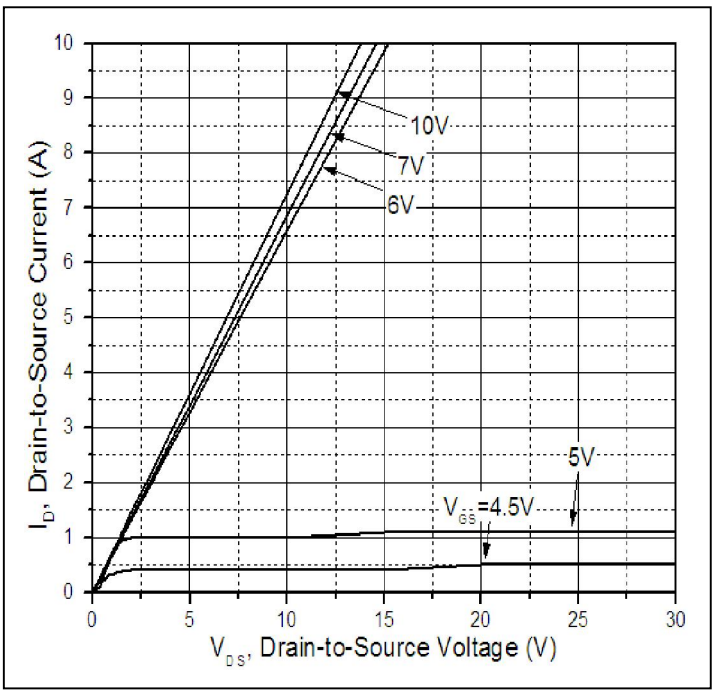


Figure 1: Typical Output Characteristics

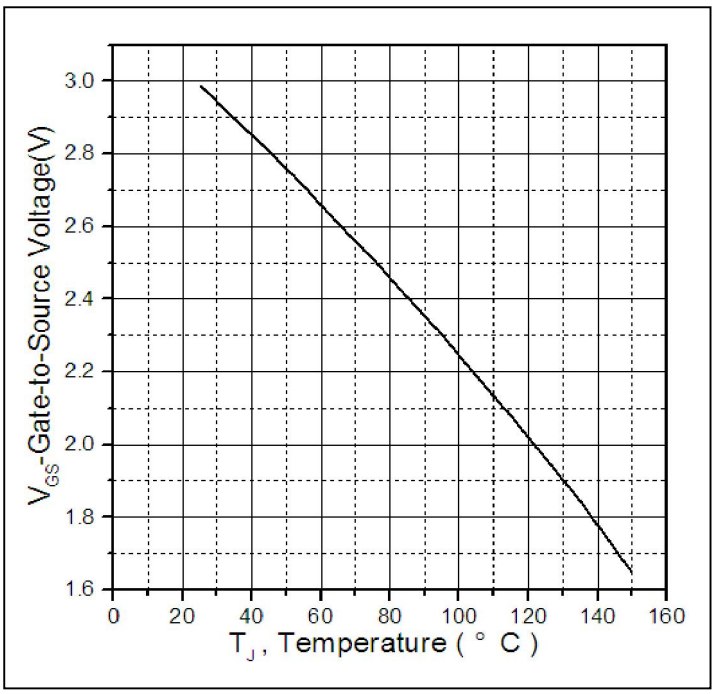


Figure 2. Gate to source cut-off voltage

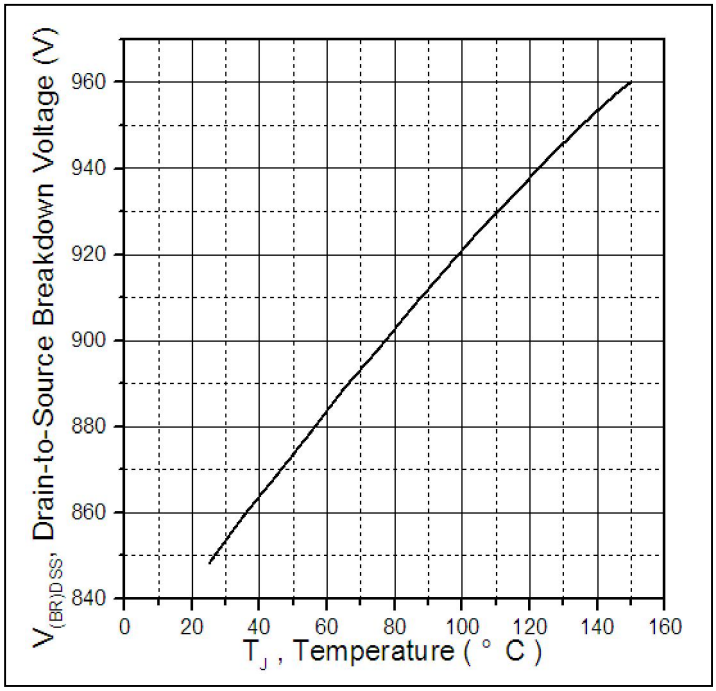


Figure 3. Drain-to-Source Breakdown Voltage Vs. Case Temperature

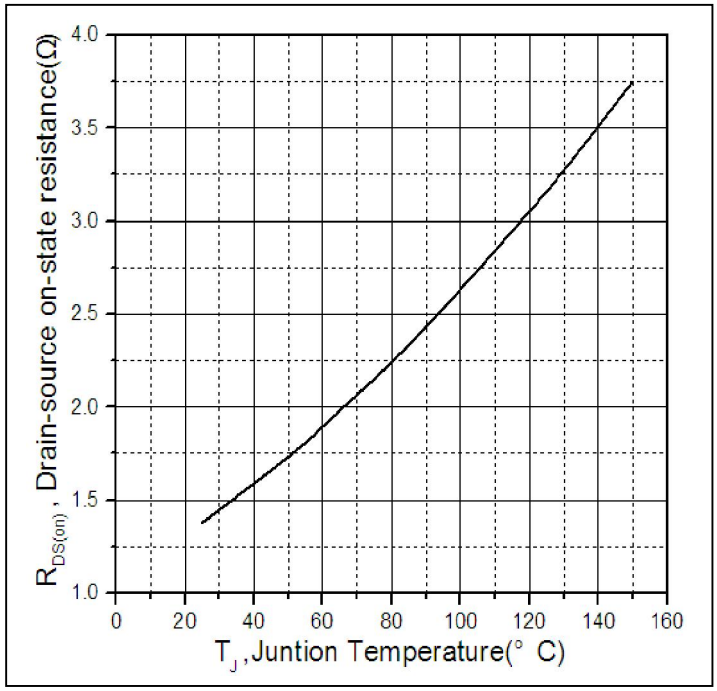


Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical Electrical and Thermal Characteristics

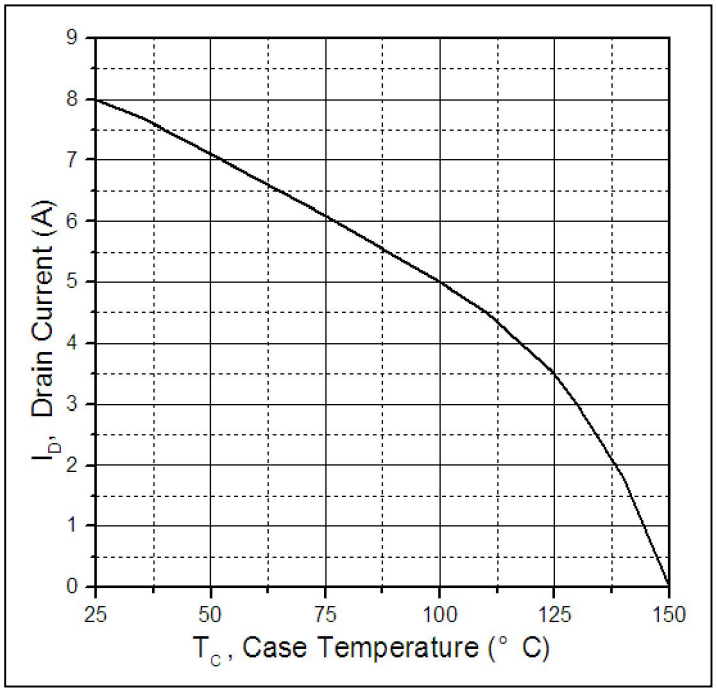


Figure 5. Maximum Drain Current Vs. Case Temperature

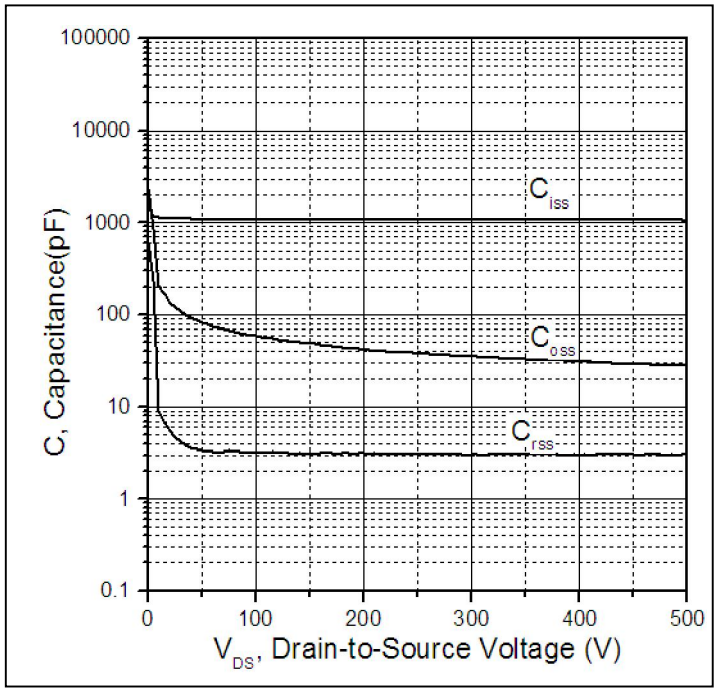


Figure 6.Typical Capacitance Vs. Drain-to-Source Voltage

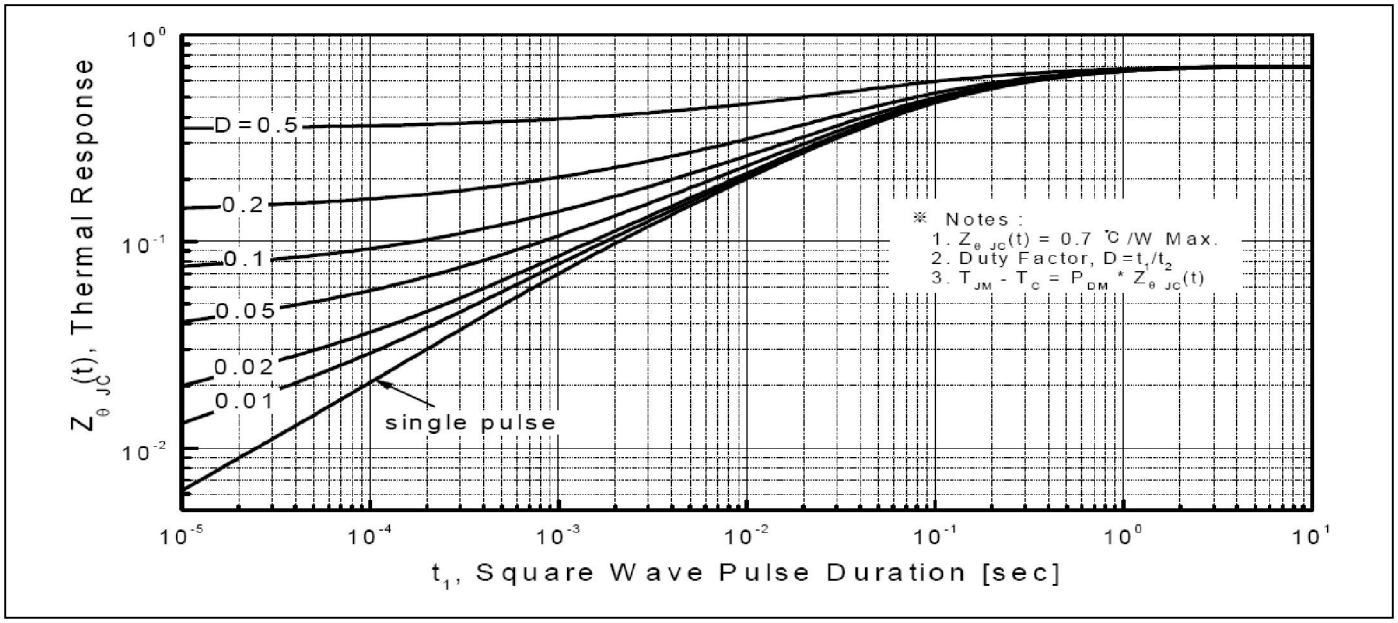
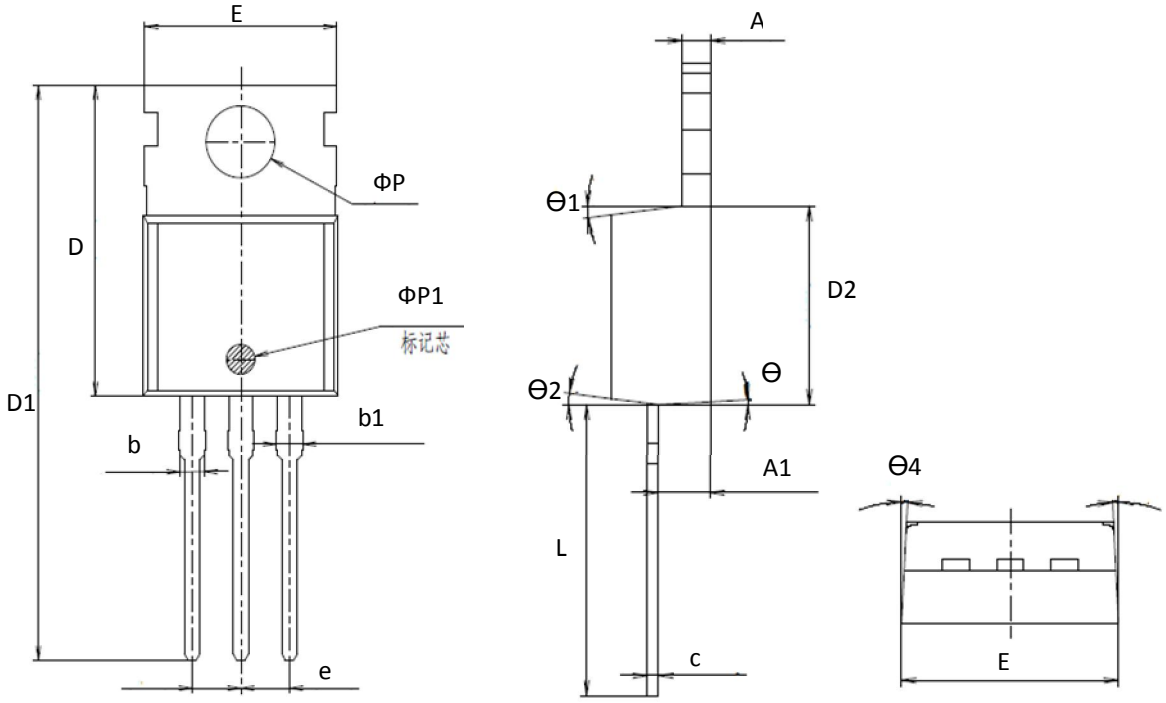


Figure7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data

TO-220 PACKAGE OUTLINE DIMENSION_GN



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	-	1.300	-	-	0.051	-
A1	2.200	2.400	2.600	0.087	0.094	0.102
b	-	1.270	-	-	0.050	-
b1	1.270	1.370	1.470	0.050	0.054	0.058
c	-	0.500	-	-	0.020	-
D	-	15.600	-	-	0.614	-
D1	-	28.700	-	-	1.130	-
D2	-	9.150	-	-	0.360	-
E	9.900	10.000	10.100	0.390	0.394	0.398
E1	-	10.160	-	-	0.400	-
ΦP	-	3.600	-	-	0.142	-
ΦP1		1.500			0.059	
e		2.54BSC			0.1BSC	
L	12.900	13.100	13.300	0.508	0.516	0.524
Θ1	-	7^0	-	-	7^0	-
Θ2	-	7^0	-	-	7^0	-
Θ3	-	3^0	-	5^0	7^0	9^0
Θ4	-	3^0	-	1^0	3^0	5^0

Ordering and Marking Information

Device Marking: SSF8N80

Package (Available)

TO-220

Operating Temperature Range

C : -55 to 150 ºC

Devices per Unit

Package Type	Units/ Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO220	50	20	1000	6	6000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T_j=125℃ to 150℃ @ 80% of Max V_{DSS}/V_{CES}/VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T_j=150℃ @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices